

NTP22N06L, NTB22N06L



Power MOSFET 22 Amps, 60 Volts, Logic Level N-Channel TO-220 and D²PAK

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

Typical Applications

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

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22 AMPERES

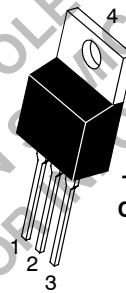
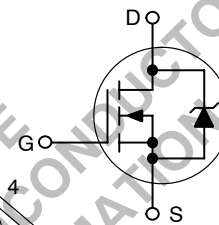
60 VOLTS

R_{DS(on)} = 65 mΩ

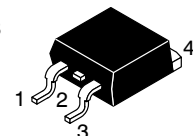
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	60	Vdc
Drain-to-Gate Voltage (R _{GS} = 10 MΩ)	V _{DGR}	60	Vdc
Gate-to-Source Voltage	V _{GS}	±10	Vdc
– Continuous	V _{GS}	±20	
– Non-Repetitive (t _p ≤ 10 ms)			
Drain Current	I _D	22	Adc
– Continuous @ T _A = 25°C	I _D	10	
– Continuous @ T _A = 100°C	I _{DM}	66	Apk
– Single Pulse (t _p ≤ 10 μs)			
Total Power Dissipation @ T _A = 25°C	P _D	60	W
Derate above 25°C		0.4	W/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C
Single Pulse Drain-to-Source Avalanche Energy – Starting T _J = 25°C (V _{DD} = 50 Vdc, V _{GS} = 5.0 Vdc, L = 1.0 mH, I _{L(pk)} = 12 A, V _{DS} = 60 Vdc, R _G = 25 Ω)	E _{AS}	72	mJ
Thermal Resistance	R _{θJC}	2.5	°C/W
– Junction-to-Case	R _{θJA}	62.5	
– Junction-to-Ambient			
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T _L	260	°C

N-Channel

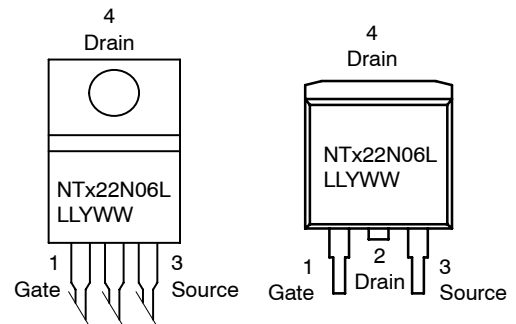


**TO-220AB
CASE 221A
STYLE 5**



**D²PAK
CASE 418B
STYLE 2**

MARKING DIAGRAMS & PIN ASSIGNMENTS



NTx22N06L = Device Code
x = P or B
LL = Location Code
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
NTP22N06L	TO-220AB	50 Units/Rail
NTB22N06L	D ² PAK	50 Units/Rail
NTB22N06LT4	D ² PAK	800/Tape & Reel

NTP22N06L, NTB22N06L

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Breakdown Voltage (Note 1.) (V _{GS} = 0 Vdc, I _D = 250 μAdc) Temperature Coefficient (Positive)	V _{(BR)DSS}	60	68.2	-	Vdc
		-	81	-	mV/°C
Zero Gate Voltage Drain Current (V _{DS} = 60 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 60 Vdc, V _{GS} = 0 Vdc, T _J = 150°C)	I _{DSS}	-	-	1.0	μAdc
		-	-	10	
Gate-Body Leakage Current (V _{GS} = ±15 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	±100	nAdc

ON CHARACTERISTICS (Note 1.)

Gate Threshold Voltage (Note 1.) (V _{DS} = V _{GS} , I _D = 250 μAdc) Threshold Temperature Coefficient (Negative)	V _{GS(th)}	1.0	1.79	2.0	Vdc
		-	5.0	-	mV/°C
Static Drain-to-Source On-Resistance (Note 1.) (V _{GS} = 5.0 Vdc, I _D = 11 Adc)	R _{DS(on)}	-	57	65	mΩ
Static Drain-to-Source On-Voltage (Note 1.) (V _{GS} = 5.0 Vdc, I _D = 22 Adc) (V _{GS} = 5.0 Vdc, I _D = 11 Adc, T _J = 150°C)	V _{DS(on)}	-	1.4	1.7	Vdc
		-	1.17	-	
Forward Transconductance (Note 1.) (V _{DS} = 7.0 Vdc, I _D = 11 Adc)	g _{FS}	-	14.6	-	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	-	490	690	pF
Output Capacitance		C _{oss}	-	167	230	
Transfer Capacitance		C _{rss}	-	56	80	

SWITCHING CHARACTERISTICS (Note 2.)

Turn-On Delay Time	(V _{DD} = 30 Vdc, I _D = 22 Adc, V _{GS} = 5.0 Vdc, R _G = 9.1 Ω) (Note 1.)	t _{d(on)}	-	10	20	ns
Rise Time		t _r	-	115	230	
Turn-Off Delay Time		t _{d(off)}	-	21	40	
Fall Time		t _f	-	56	120	
Gate Charge	(V _{DS} = 48 Vdc, I _D = 22 Adc, V _{GS} = 5.0 Vdc) (Note 1.)	Q _T	-	10.4	20	nC
		Q ₁	-	2.5	-	
		Q ₂	-	7.0	-	

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage	(I _S = 22 Adc, V _{GS} = 0 Vdc) (Note 1.) (I _S = 22 Adc, V _{GS} = 0 Vdc, T _J = 150°C)	V _{SD}	-	1.03	1.2	Vdc
			-	0.98	-	
Reverse Recovery Time	(I _S = 22 Adc, V _{GS} = 0 Vdc, di _S /dt = 100 A/μs) (Note 1.)	t _{rr}	-	42	-	ns
		t _a	-	26	-	
		t _b	-	16	-	
Reverse Recovery Stored Charge		Q _{RR}	-	0.060	-	μC

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperatures.

NTP22N06L, NTB22N06L

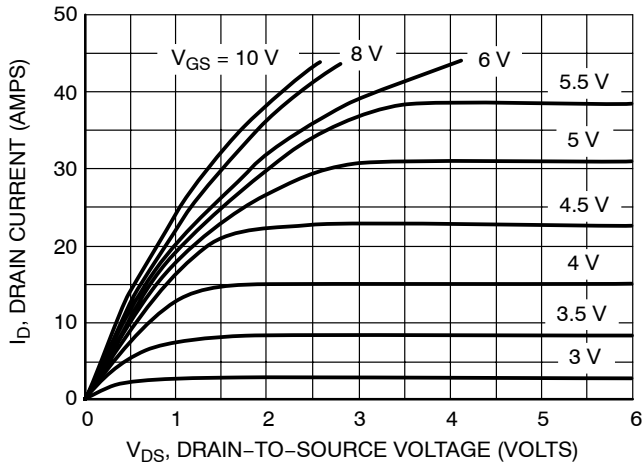


Figure 1. On-Region Characteristics

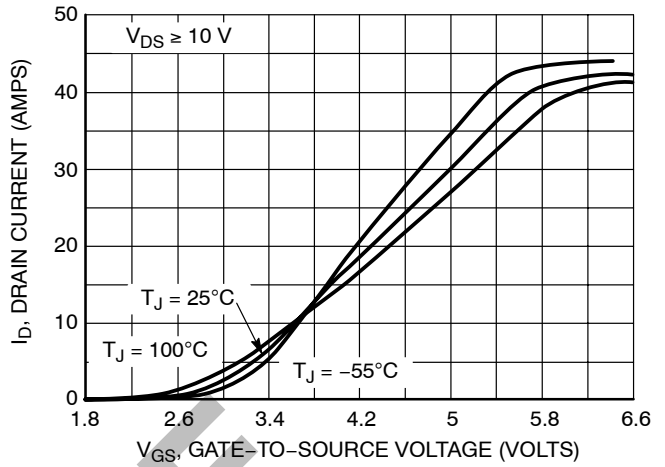


Figure 2. Transfer Characteristics

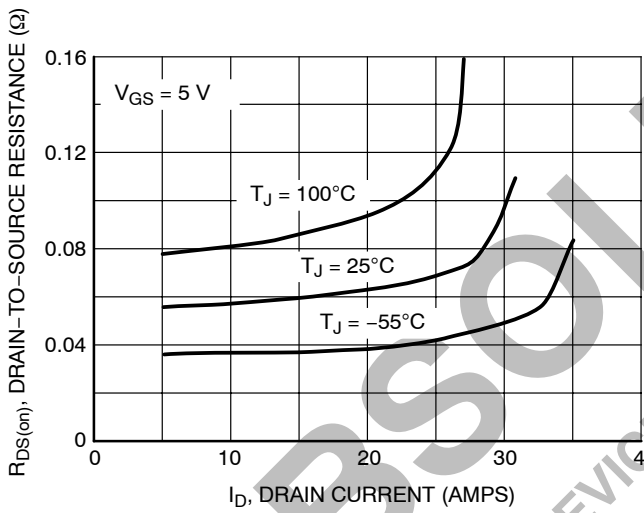


Figure 3. On-Resistance versus Gate-to-Source Voltage

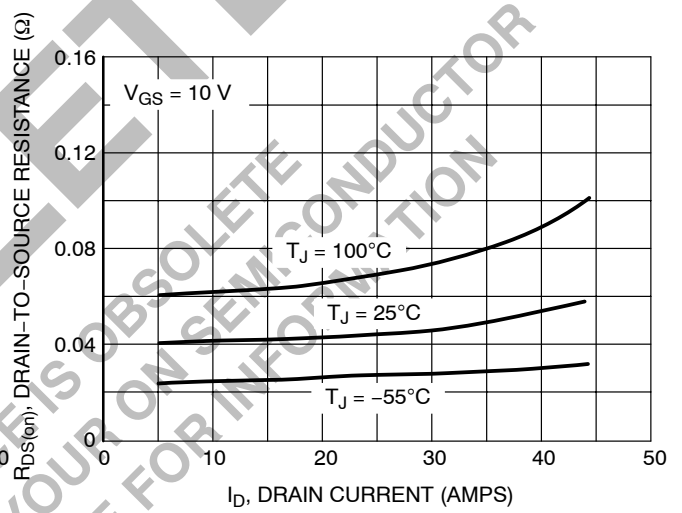


Figure 4. On-Resistance versus Drain Current and Gate Voltage

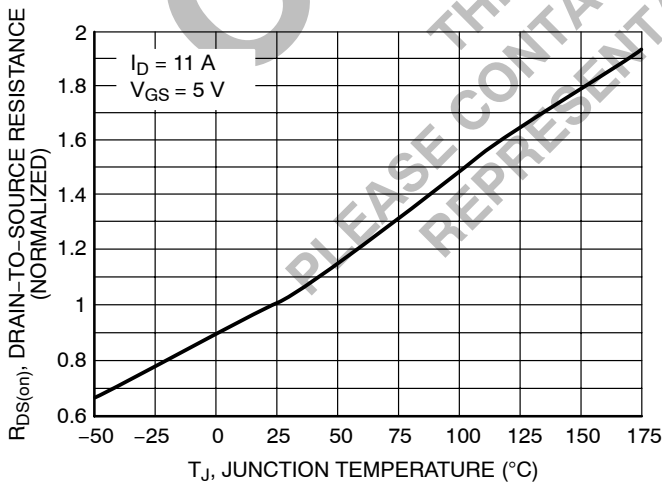


Figure 5. On-Resistance Variation with Temperature

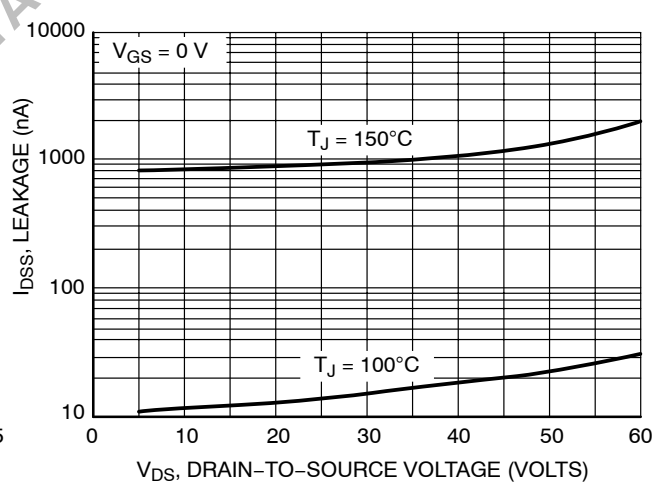


Figure 6. Drain-to-Source Leakage Current versus Voltage

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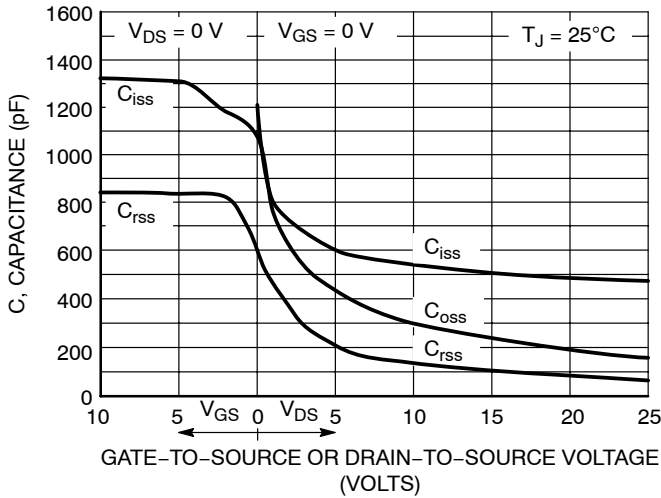


Figure 7. Capacitance Variation

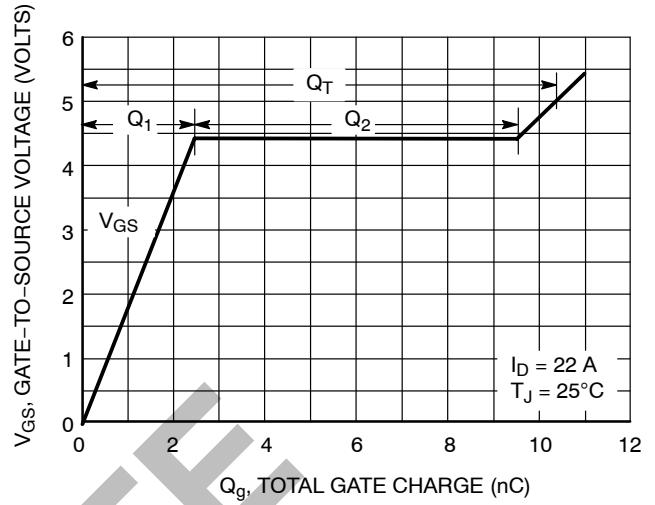


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

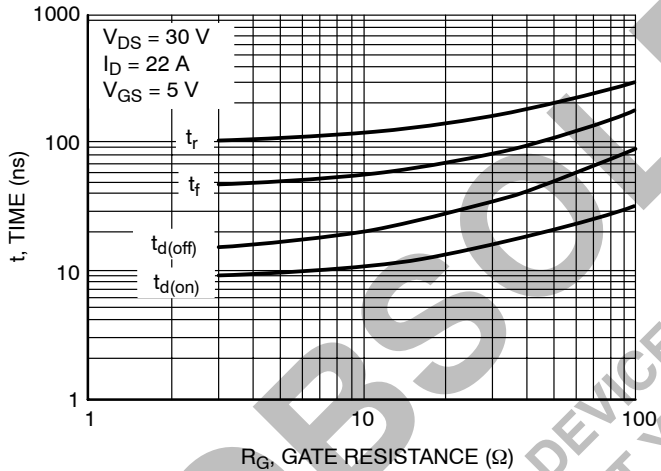


Figure 9. Resistive Switching Time Variation versus Gate Resistance

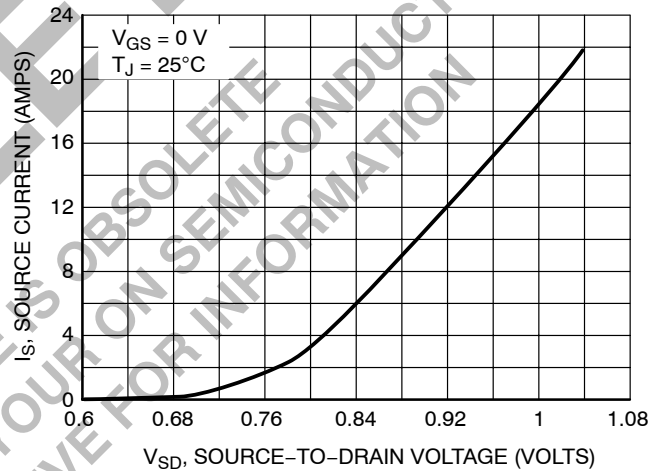


Figure 10. Diode Forward Voltage versus Current

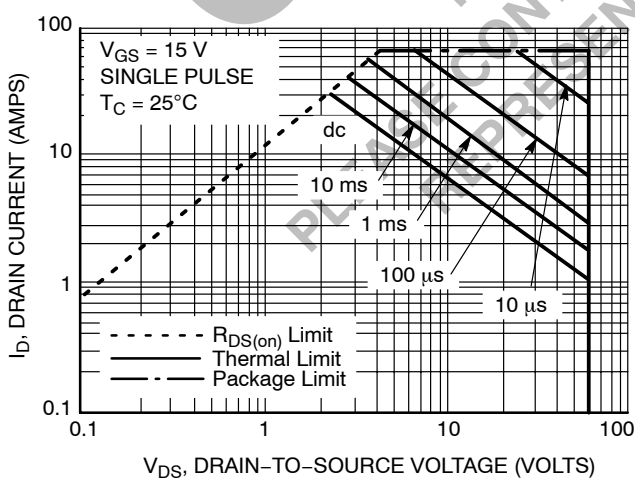


Figure 11. Maximum Rated Forward Biased Safe Operating Area

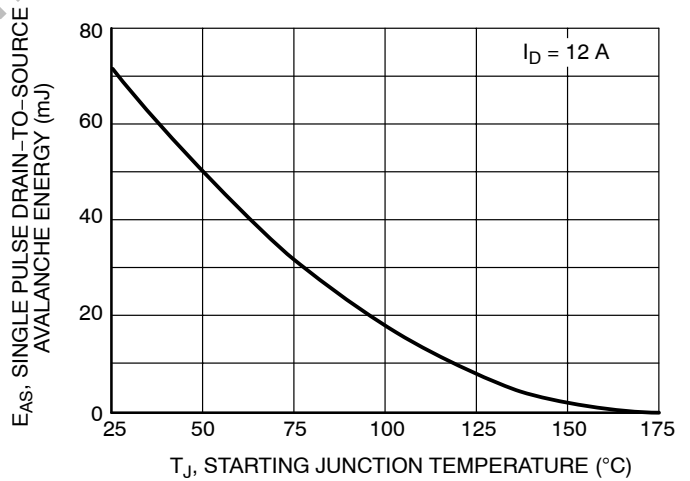


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

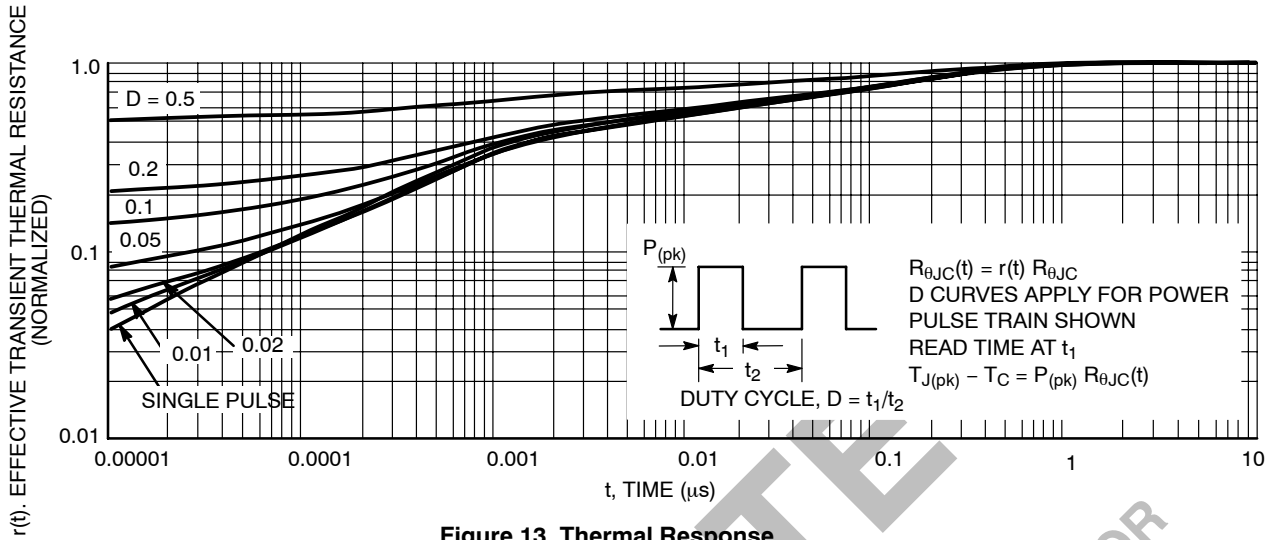


Figure 13. Thermal Response

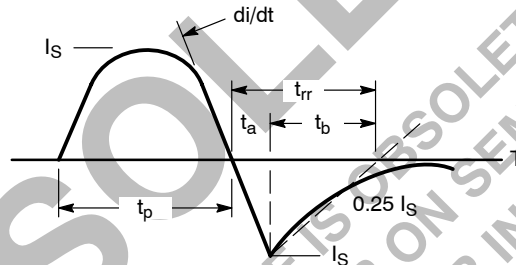
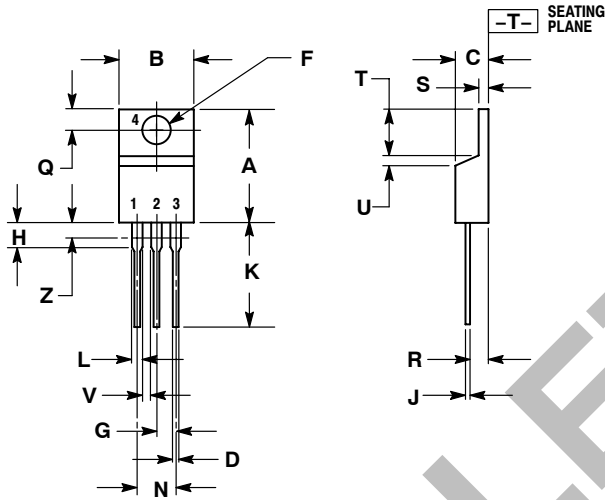


Figure 14. Diode Reverse Recovery Waveform

NTP22N06L, NTB22N06L

PACKAGE DIMENSIONS

TO-220 THREE-LEAD
TO-220AB
CASE 221A-09
ISSUE AA



NOTES:

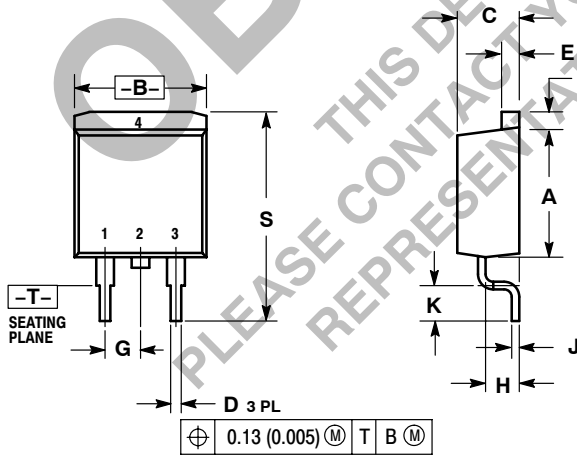
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.89	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 5:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

D²PAK
CASE 418B-03
ISSUE D



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

OBSOLETE
THIS DEVICE IS OBSOLETE
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